



SHEET 1 OF 1

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Substitute for form 1449/PTO)

ATTY. DOCKET NO.
071971-0643SERIAL NO.
10/584,617APPLICANT
Shunsaku MURAOKA, et al.FILING DATE
June 26, 2006GROUP
2824**U.S. PATENT DOCUMENTS**

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		US			
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FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Code ³ -Number 4-Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
		Korean Office Action, issued in Korean Patent Application No. 10-2006-7013643, dated on March 12, 2008
		ZHUANG et al. "Novel Colossal Magnetoresistive Thin Film Nonvolatile Resistance random Access Memory (RRAM)" IEEE, IEDM, 2002, 193-196

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.